

CLAIMS

1.-18. (Canceled).

19. (New) A method for high rate oxide chemical mechanical planarization of a film comprising a dielectric material, the method comprising the steps of:

- i) providing a substrate having a surface and a polishing pad, said surface having a film of dielectric material and being in movable contact with the polishing pad;
- ii) providing a composition for oxide chemical mechanical planarization comprising a) an abrasive; b) a fluoride salt; and c) between 0.005% and 0.03% of an acetylenic alcohol comprising at least two hydroxyl substituents; and
- iii) polishing the substrate at a high rate with the composition to effect at least partial planarization of the film.

20. (New) The method of claim 19 wherein the fluoride salt is present in an amount between 0.005 weight percent up to about 0.1 weight percent, and the abrasive comprises silica in an amount between 10% and 35% by weight based on the weight of the composition.

21. (New) The method of claim 19 wherein the dielectric material is silicon dioxide and the removal rate of the silicon dioxide is at least 3707 angstroms per minute.

22. (New) The method of claim 19 wherein the fluoride salt is present in an amount of about 0.004%

23. (New) The method of claim 19 wherein the substrate surface consists a film of silicon oxide.

24. (New) The method of claim 19 wherein the substrate surface comprises a film of low-k material having a dielectric constant less than 3.3.

25. (New) The method of claim 19 wherein the substrate is a film of silicon oxide having silicon nitride features thereon.
26. (New) The method of claim 19 wherein the substrate is a film formed from plasma enhanced tetraethoxysilane.
27. (New) The method of claim 19 wherein the acetylenic alcohol of the composition is 2,4,7,9-tetramethyl-5-decyn-4,7-diol.
28. (New) The method of claim 19 wherein the acetylenic alcohol of the composition is a C₄-C₂₂ alkyne.
29. (New) The method of claim 28 wherein the acetylenic alcohol of the composition is a C₁₂-C₁₆ alkyne.
30. (New) The method of claim 19 wherein the abrasive is colloidal silica.
31. (New) The method of claim 19 wherein the composition is free of oxidizing agents.
32. (New) A method for oxide chemical mechanical planarization of a film comprising a dielectric material, the method comprising the steps of:
- i) providing a substrate having a surface and a polishing pad, said surface comprising a film of dielectric material being in movable contact with the polishing pad;
 - ii) providing a composition for oxide chemical mechanical planarization consisting essentially of a) a silica abrasive; b) a fluoride salt; and c) an acetylenic alcohol comprising at least two hydroxyl substituents; and
 - iii) polishing the substrate with the composition to effect at least partial planarization of the film.

32. (New) The method of claim 33 wherein the composition is free of oxidizing agents.

33. (New) The method of claim 33 wherein the composition consists of a silica abrasive; b) a fluoride salt; and c) an acetylenic alcohol comprising at least two hydroxyl substituents.